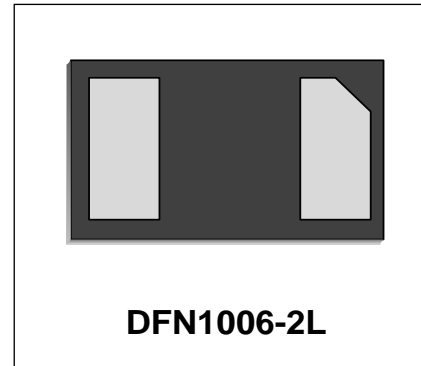


### Features

- Small Body Outline Dimensions:
- Protects one I/O line
- Working Voltage: 12 V
- Low Leakage Current
- AEC-Q101 Qualified



### IEC COMPATIBILITY (EN61000-4)

- IEC 61000-4-2 (ESD)  $\pm 30\text{kV}$  (air),  $\pm 30\text{kV}$  (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20 $\mu\text{s}$ )

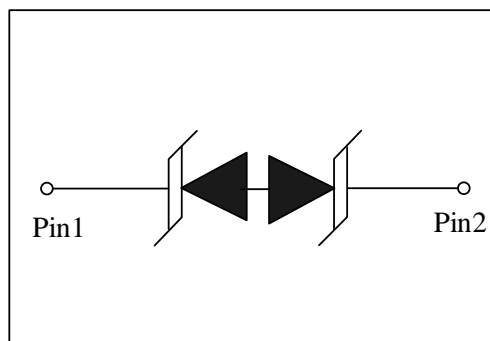
### Mechanical Characteristics

- DFN1006-2L package
- Marking : Marking Code
- Packaging : Tape and Reel per EIA 481
- RoHS Compliant

### Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants (PDAs)
- Notebooks & Handhelds
- Portable Instrumentation
- Digital Cameras
- MP3 Players

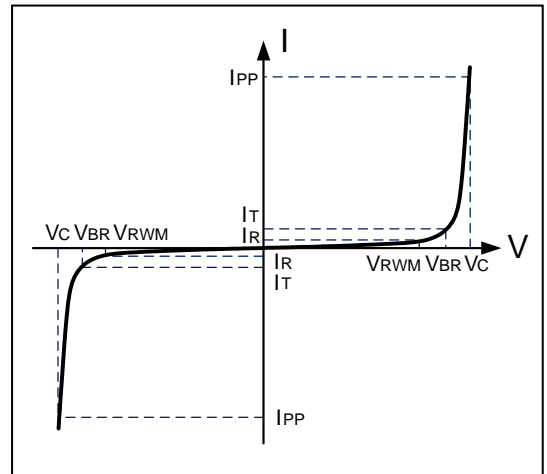
### Schematic & PIN Configuration



Absolute Maximum Rating			
Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	$P_{PP}$	130	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ )	$I_{PP}$	5	A
Operating Temperature	$T_J$	-55 to +125	°C
Storage Temperature	$T_{STG}$	-55 to +150	°C

**Electrical Parameters (T=25°C)**

Symbol	Parameter
$I_{PP}$	Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Reverse Stand-Off Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current



**Electrical Characteristics**

WE12DF-B-AT						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	$V_{RWM}$				12	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T=1mA$	13.3			V
Reverse Leakage Current	$I_R$	$V_{RWM}=12V, T=25°C$			200	nA
Clamping Voltage	$V_C$	$I_{PP}=5A, t_p=8/20\mu s$		24	26	V
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP} = 4A$ $t_p = 0.2/100ns$		18.5		V
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP} = 16A$ $t_p = 0.2/100ns$		24.6		V
Dynamic Resistance <sup>1,2</sup>	$R_{DYN}$	TLP=0.2/100ns		0.51		Ω
Junction Capacitance	$C_j$	$V_R = 0V, f = 1MHz$		10	15	pF

**Note:** 1、 TLP Setting :  $t_p=100ns, t_r=0.2ns, I_{TLP}$  and  $V_{TLP}$  sample window: $t_1=70ns$  to  $t_2=90ns$ .  
 2、 Dynamic resistance calculated from  $I_{PP}=4A$  to  $I_{PP}=16A$  using "Best Fit"

Typical Characteristics

Figure 1: Peak Pulse Power Vs Pulse Time

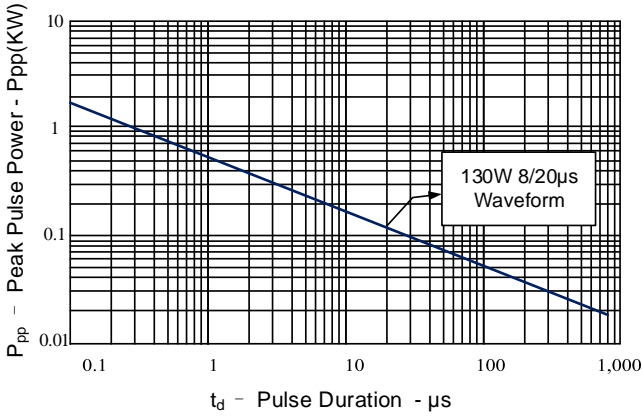


Figure 2: Power Derating Curve

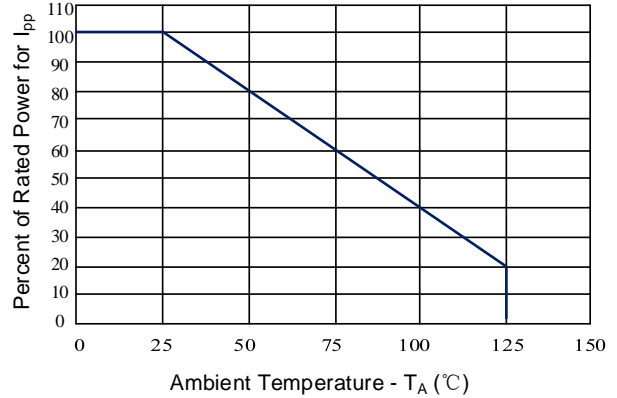


Figure 3: Clamping Voltage vs. Peak Pulse Current

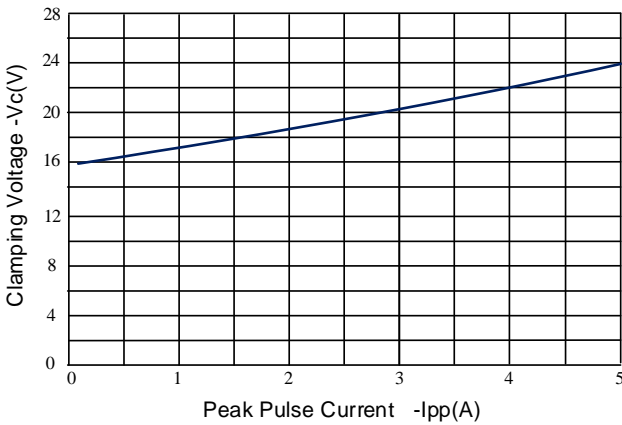


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

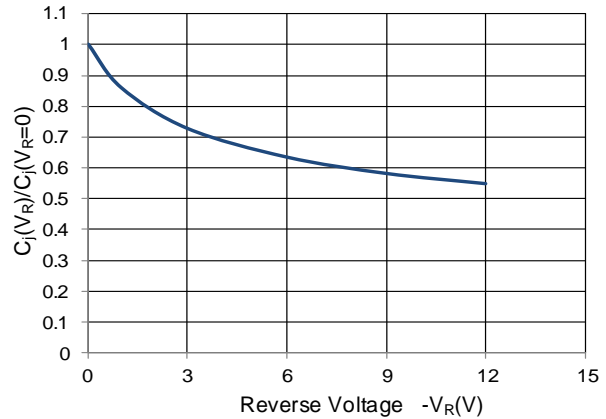


Figure 5: TLP Positive I-V Curve

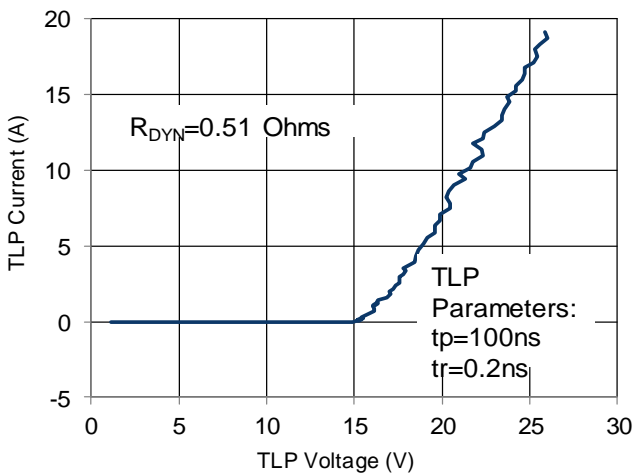
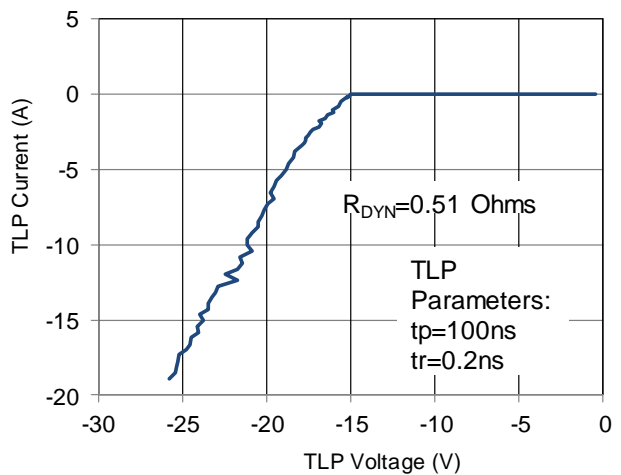
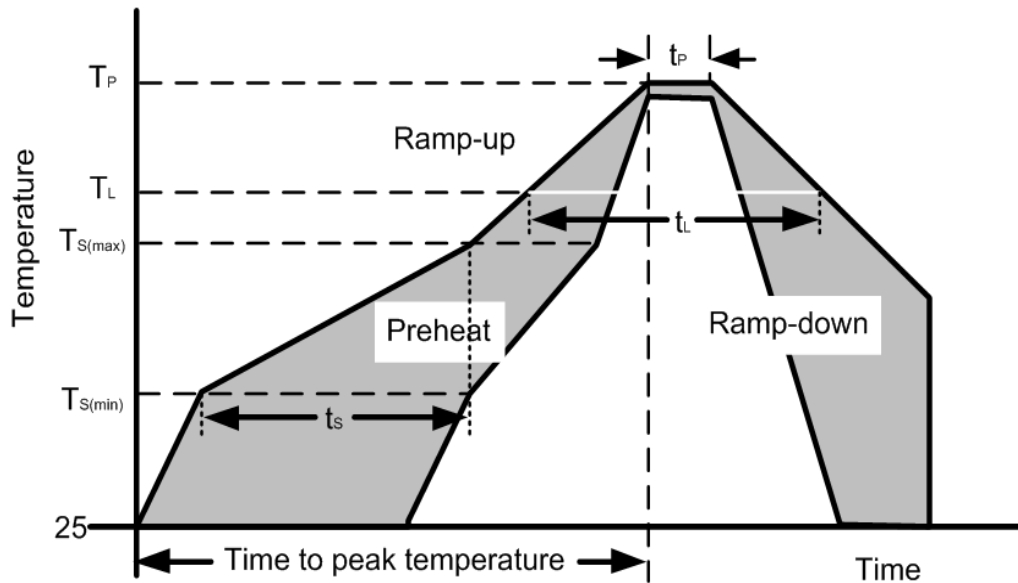


Figure 6: TLP Negative I-V Curve



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	Temperature Min ( $T_{S(min)}$ )	150°C
	Temperature Max ( $T_{S(max)}$ )	200°C
	Time (min to max) ( $t_s$ )	60 – 190 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{S(max)}$ to $T_L$ —Ramp-up Rate		5°C/second max
Reflow	Temperature ( $T_L$ ) (Liquidus)	217°C
	Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_P$ )		260+0/-5 °C
Time within actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_P$ )		8 minutes Max.
Do not exceed		280°C



Outline Drawing –DFN1006-2L

**PACKAGE OUTLINE**

BOTTOM VIEW

DFN1006-2L

SYMBOL	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.50	0.55
C	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05REF		
h	0.07	0.12	0.17

**Land Pattern**

**Marking Codes**

Part Number	WE12DF-B-AT
Marking Code	AF

**Package Information**

Qty: 10k/Reel

**CONTACT INFORMATION**

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For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.  
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.  
Users should verify actual device performance in their specific applications.